

Notice of References Cited			Application/Control No.	Applicant(s)/Patent Under Reexamination NAKAMURA ET AL.	
			Examiner DANIEL ZEILBERGER	Art Unit 2624	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,828,773	10-1998	Setlak et al.	382/126
*	B	US-2002/0014530	02-2002	Iihama, Tomomi	235/454
*	C	US-2001/0030324	10-2001	Morikawa et al.	257/59
*	D	US-6,240,199	05-2001	Manchanda et al.	382/124
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ma, Making Silicon Nitride Film a Viable Gate Dielectric, March 1998, IEEE Transactions on Electron Devices, Vol 45, No 3, Pgs 680-690
	V	English language translation of the Text of the First Office Action Issued in Chinese Patent Application No. 03152474.5
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.